

**HIGH ISOLATION VOLTAGE
SOP PHOTOCOUPLER**

–NEPOC™ Series–

DESCRIPTION

The PS2801-1 and PS2801-4 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor in a plastic SOP for high density applications.

This package has shield effect to cut off ambient light.

FEATURES

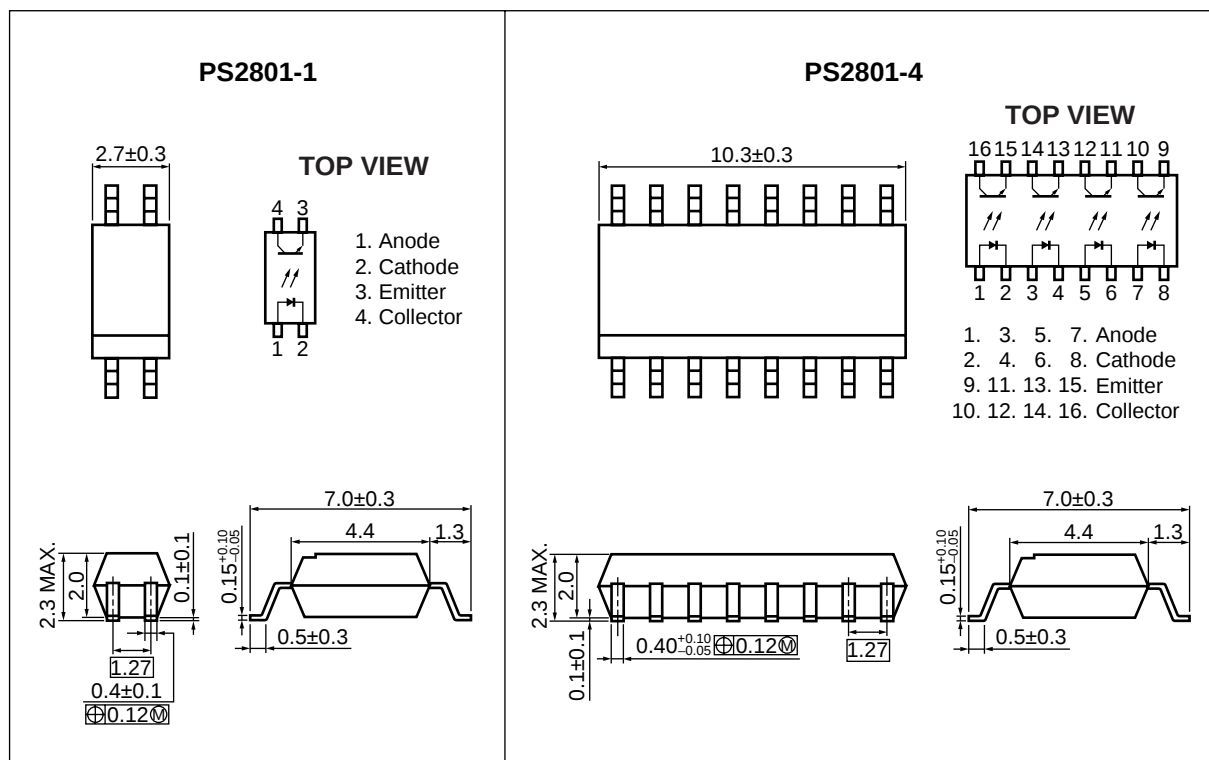
- High isolation voltage ($BV = 2\,500\text{ V r.m.s.}$)
- Small and thin package (4,16-pin SOP, Pin pitch 1.27 mm)
- High collector to emitter voltage ($V_{CEO} = 80\text{ V}$)
- High-speed switching ($t_r = 3\text{ }\mu\text{s TYP.}$, $t_f = 5\text{ }\mu\text{s TYP.}$)
- UL approved: File No. E72422 (S)
- ★ • VDE0884 approved (Option): PS2801-4 only
- Operating number of taping product: PS2801-1-F3, F4, PS2801-4-F3, F4

APPLICATIONS

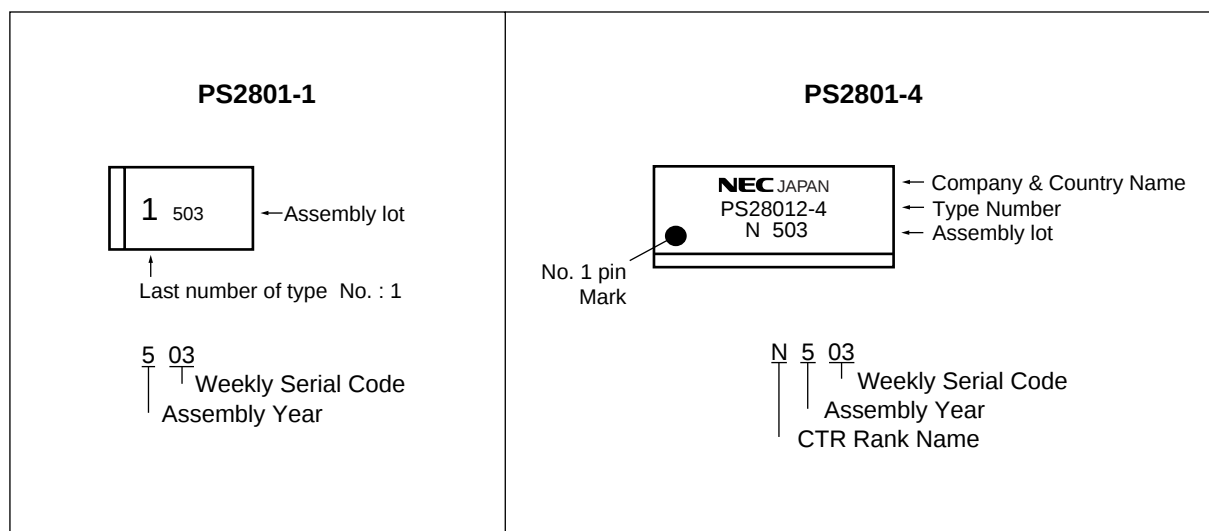
- Programmable logic controllers
- Measuring instruments
- Power supply
- Hybrid IC

The information in this document is subject to change without notice.

★ PACKAGE DIMENSIONS (in millimeters)



MARKING



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter		Symbol	Ratings		Unit
			PS2801-1	PS2801-4	
Diode	Forward Current (DC)	I_F	50		mA
	Reverse Voltage	V_R	6		V
	Power Dissipation Derating	$\Delta P_D/^{\circ}\text{C}$	0.6	0.8	mW/ $^{\circ}\text{C}$
	Power Dissipation	P_D	60	80	mW/ch
	Peak Forward Current ^{*1}	I_{FP}	1		A
Transistor	Collector to Emitter Voltage	V_{CEO}	80		V
	Emitter to Collector Voltage	V_{ECO}	6		V
	Collector Current	I_C	50		mA/ch
	Power Dissipation Derating	$\Delta P_C/^{\circ}\text{C}$	1.2		mW/ $^{\circ}\text{C}$
	Power Dissipation	P_C	120		mW/ch
Isolation Voltage ^{*2}		BV	2 500		Vr.m.s.
Operating Ambient Temperature		T_A	-55 to +100		$^{\circ}\text{C}$
Storage Temperature		T_{stg}	-55 to +150		$^{\circ}\text{C}$

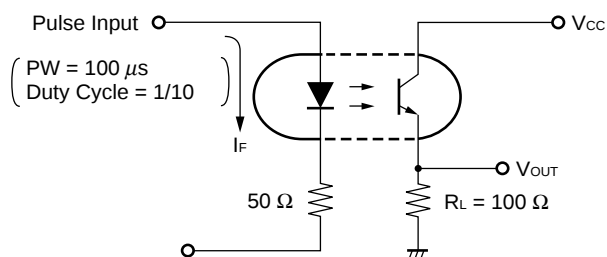
***1** PW = 100 μs , Duty Cycle = 1 %

***2** AC voltage for 1 minute at $T_A = 25\text{ }^{\circ}\text{C}$, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

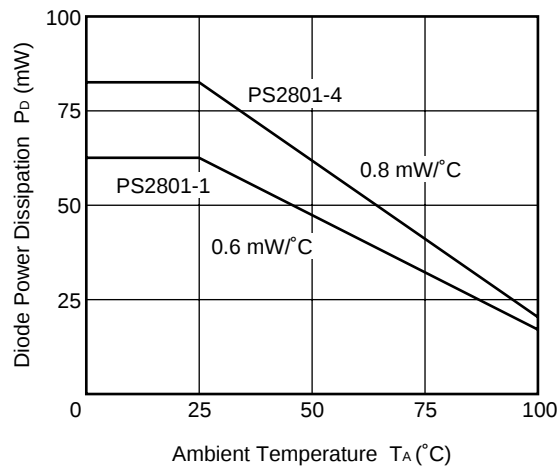
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V _F	I _F = 5 mA		1.1	1.4	V
	Reverse Current	I _R	V _R = 5 V			5	μA
	Terminal Capacitance	C _t	V = 0 V, f = 1.0 MHz		30		pF
Transistor	Collector to Emitter Dark Current	I _{CEO}	V _{CE} = 80 V, I _F = 0 mA			100	nA
Coupled	Current Transfer Ratio (I _C /I _F)	CTR	I _F = 5 mA, V _{CE} = 5 V	80		600	%
	Collector Saturation Voltage	V _{CE(sat)}	I _F = 10 mA, I _C = 2 mA			0.3	V
	Isolation Resistance	R _{I-O}	V _{I-O} = 1.0 kV _{DC}	10 ¹¹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1.0 MHz		0.4		pF
	Rise Time ^{*1}	t _r	V _{CC} = 5 V, I _C = 2 mA, R _L = 100 Ω		3		μs
	Fall Time ^{*1}	t _f			5		

*1 Test circuit for switching time

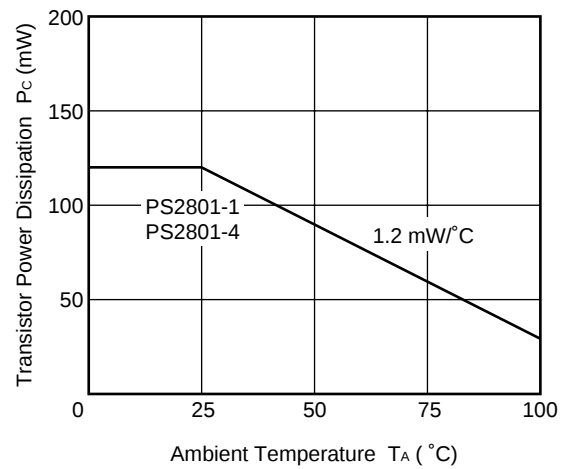


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

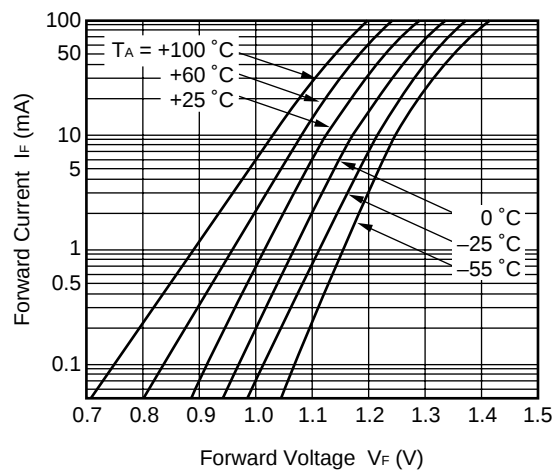
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



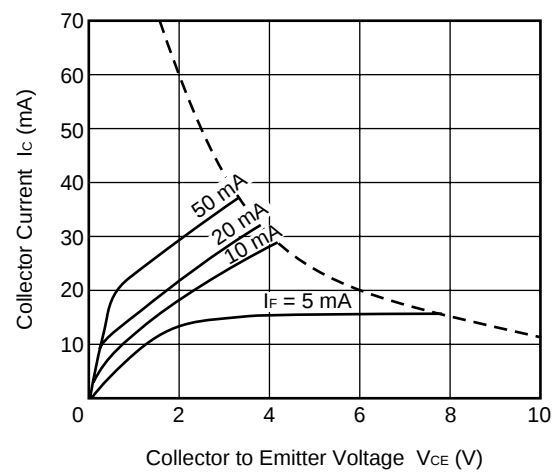
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



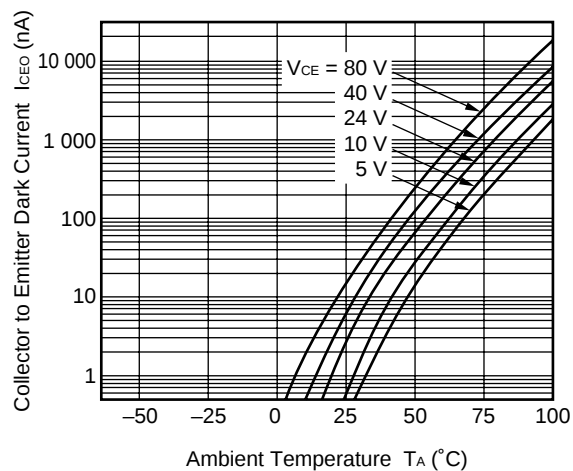
FORWARD CURRENT vs. FORWARD VOLTAGE



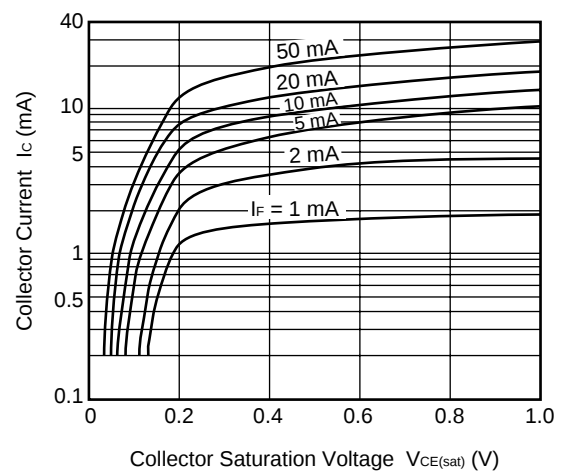
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



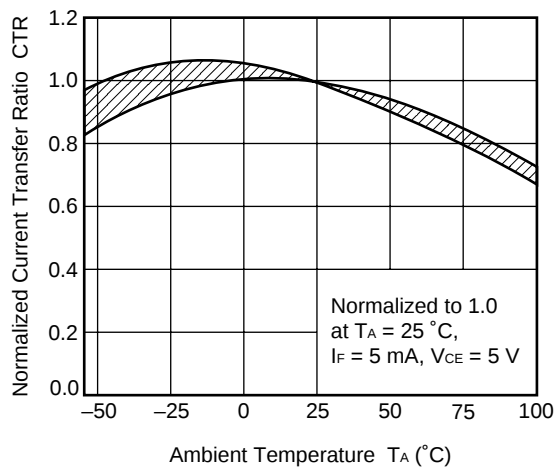
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



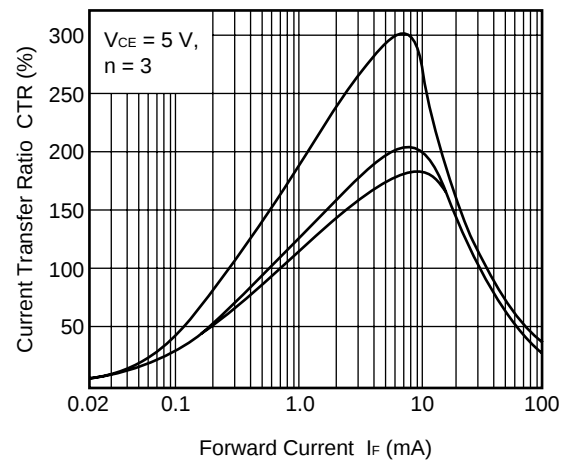
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



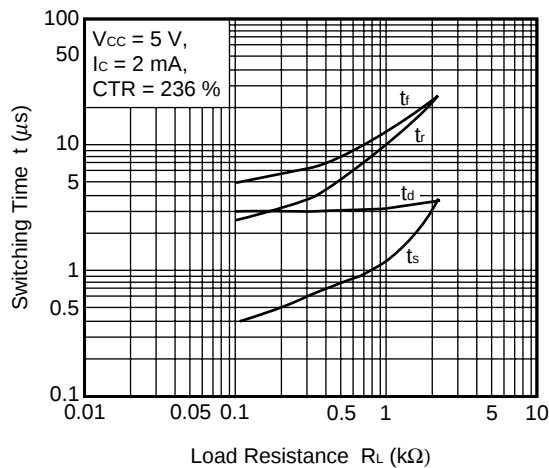
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



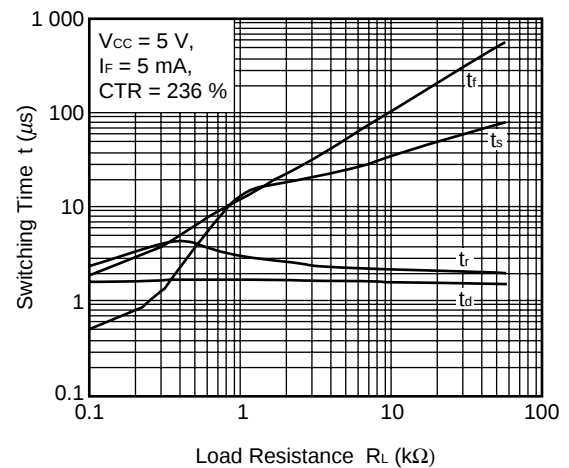
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



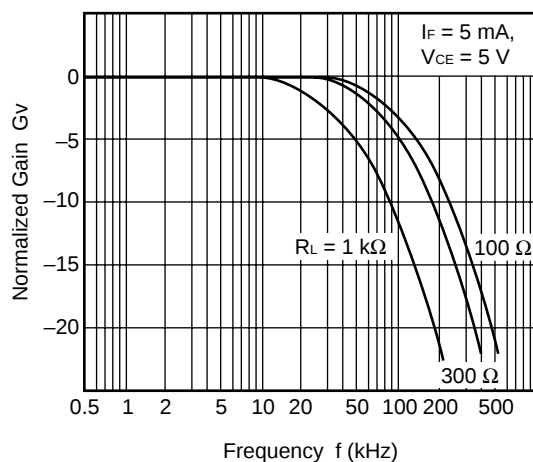
SWITCHING TIME vs. LOAD RESISTANCE



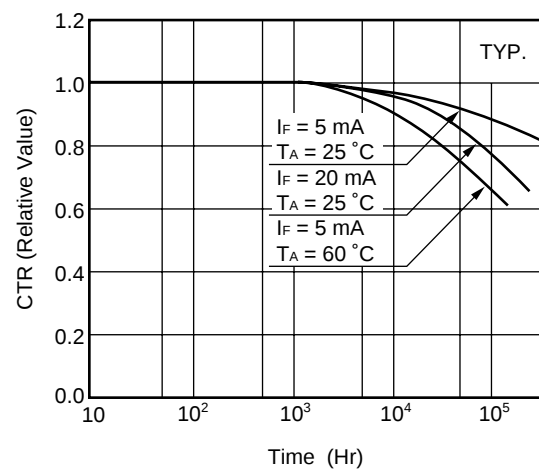
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



LONG TERM CTR DEGRADATION

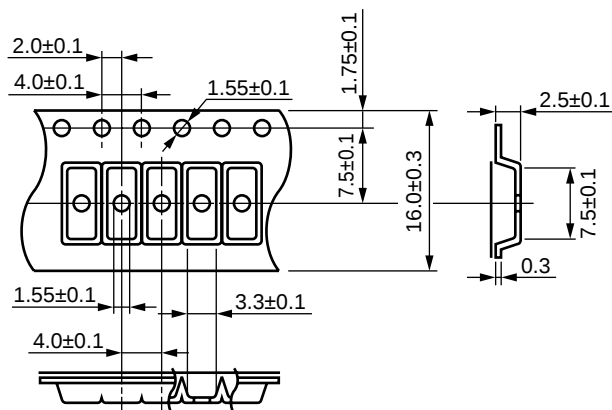


Remark The graphs indicate nominal characteristics.

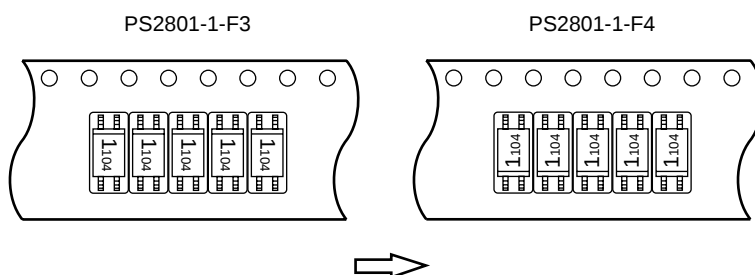
TAPING SPECIFICATIONS (in millimeters)

PS2801-1

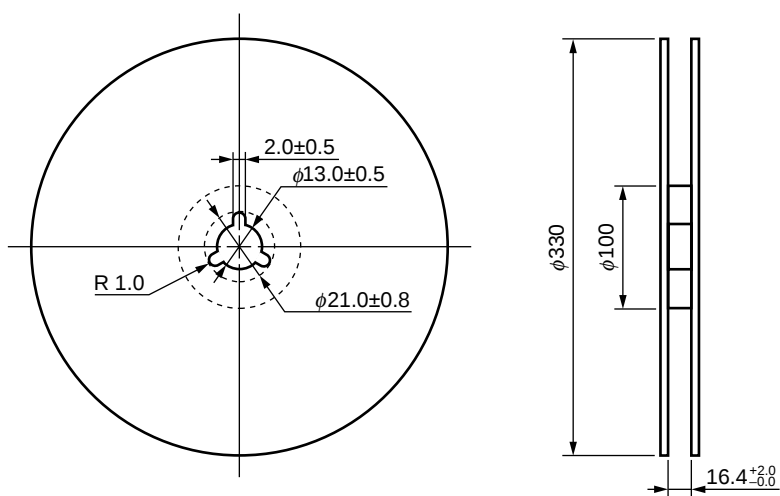
Outline and Dimensions (Tape)



Tape Direction



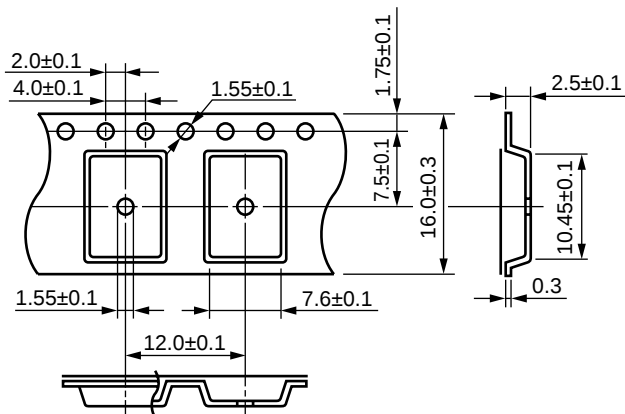
Outline and Dimensions (Reel)



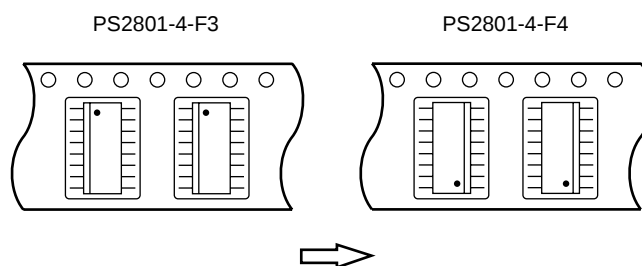
Packing: 3 500 pcs/reel

PS2801-4

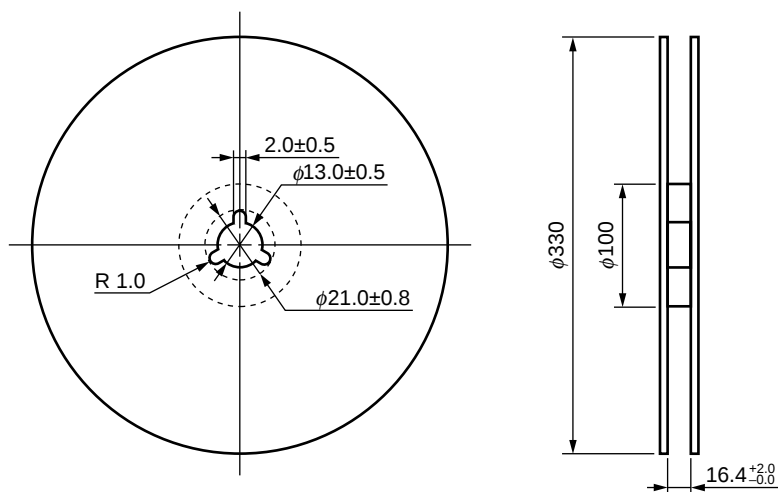
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



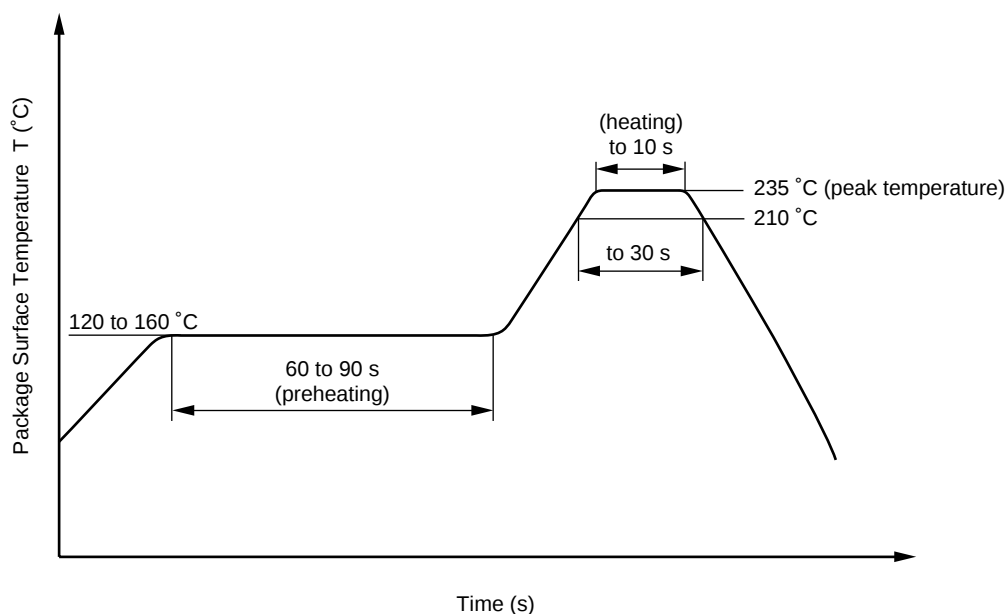
Packing: 2 500 pcs/reel

RECOMMENDED SOLDERING CONDITIONS

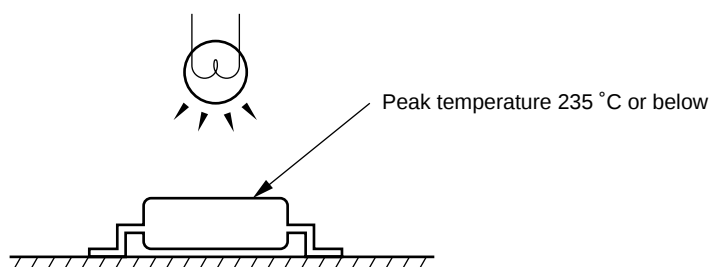
(1) Infrared reflow soldering

- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C 30 seconds or less
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



★ **Caution** Avoid removing the residual flux with chlorine-based cleaning solvent after a reflow process.

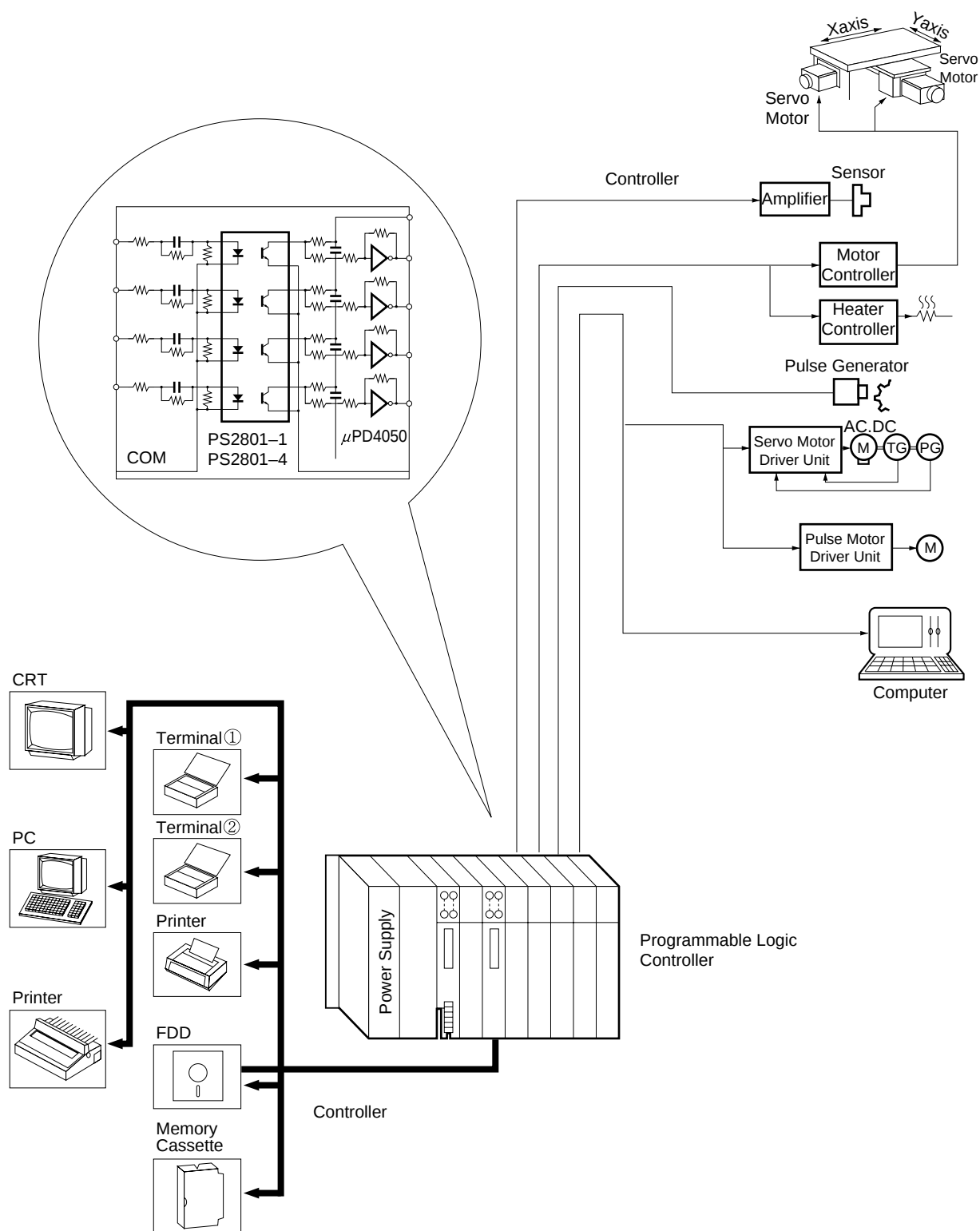


(2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time 10 seconds or less
- Number of times One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

PROGRAMMABLE LOGIC CONTROLLERS EXAMPLE

Purpose: In-out interface



[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Anti-radioactive design is not implemented in this product.

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